

# **isc Silicon PNP Power Transistor**

**BD136** 

#### **DESCRIPTION**

- DC Current Gain-
  - : h<sub>FE</sub>= 40(Min)@ I<sub>C</sub>= -0.15A
- · Collector-Emitter Sustaining Voltage -
  - : V<sub>CEO(SUS)</sub>= -45V(Min)
- Complement to type BD135
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



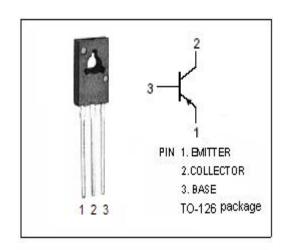
 Designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

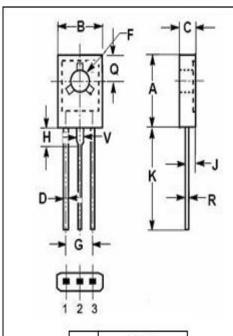


ABSOLUTE MAXIMUM RATINGS(Ta-25 C)				
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-45	V	
VCEO	Collector-Emitter Voltage	-45	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
Ic	Collector Current-Continuous	-1.5	А	
I <sub>B</sub>	Base Current-Continuous	-0.5	А	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.25	\A/	
	Collector Power Dissipation @ T <sub>C</sub> =25 °C	12.5	W	
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	10	°C/W
R <sub>th j-a</sub>	Thermal Resistance,Junction to Ambient	100	°C/W





	mm	
DIM	MIN	MAX
Α	10.70	10.95
В	7.70	7.90
С	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
Н	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
٧	1.17	1.37



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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -30mA ; I <sub>B</sub> =0	-45			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -0.5A; I <sub>B</sub> = -50mA			-0.5	V		
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V			-1.0	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -30V; I <sub>E</sub> = 0 V <sub>CB</sub> = -30V; I <sub>E</sub> = 0,T <sub>C</sub> =125°C			-0.1 -10	μА		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> =0			-10	μА		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -5mA ; V <sub>CE</sub> = -2V	25					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -2V	25					
h <sub>FE-3</sub>	DC Current Gain	Ic= -0.15A ; V <sub>CE</sub> = -2V	40		250			



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